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<b>Substitute for form 1449B/PTO</b> <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> Date Submitted: 1/7/05 (use as many sheets as necessary)		<b>Complete if Known</b>	
		Application Number	10/784,586
		Filing Date	02/23/2004
		First Named Inventor	Harry A. ATWATER et al.
		Group Art Unit	1764
		Examiner Name	Unassigned
Sheet 1 of 7		Attorney Docket Number	047071-0109

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		Number	Kind Code <sup>2</sup> (if known)			
SA	A1	5,882,987		SRIKRISHNAN	08/26/1997	
	A2	6,150,239		GOESSELE et al.	09/30/1998	
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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
SA	A15	EP	0 060 103			04/17/1985		
SA	A16	WO	01/03172			01/11/2001		

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SA	A17	CURTIS et al., "Integration of the UOP/HYDRO MTO Process into Ethylene Plants," 10 <sup>th</sup> Ethylene Producers' Conference, 1998, pp. 54-85		
SA	A18	BETT et al., III-V Compounds for Solar Cell Applications, Appl. Phys. A, 1999, pp. 119-129, Vol. 69, Springer-Verlag (published online: 24 June 1999)		
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	A53	ZAHLER J.M., Materials Integration by Wafer Bonding and Layer Transfer, (Presentation), 13 pages, MRS 2004 Spring Meeting (04/2004)	
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	A58	ZAHLER et al., GE Layer Transfer to Si for Photovoltaic Applications, (Presentation), 14 pages, MRS 2001 Spring Conference, (04/2001)	
SA	A59	ZAHLER et al., Wafer Bonding and Layer Transfer Processes for A 4-Junction Solar Cell, (Presentation) 29 <sup>th</sup> IEEE Photovoltaic Specialists Conference, New Orleans, USA, (05/2002)	

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  Date Submitted: 1/7/05  <i>(use as many sheets as necessary)</i>				Application Number	10/784,586
				Filing Date	02/23/2004
				First Named Inventor	Harry A. ATWATER et al.
				Group Art Unit	1764
				Examiner Name	Unassigned
Sheet	7	of	7	Attorney Docket Number	047071-0109

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				

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SA	A60	ZAHLER et al., Ge/Si Wafer Bonded Epitaxial Templates for GaAs/Si Heterostructures, (Abstract), MRS 2002 Fall Meeting, (11/2002)	
SA	A61	MORRAL et al., Bonding and Layer Transfer Process of InP on Silicon for the Elaboration of the Bottom Double Heterostructure of 4-Junction High Efficiency Solar Cells, (Abstract), MRS 2002 Fall Meeting, (11/2002)	
SA	A62	MORRAL et al., Assessment of Optical and Structural Properties of III-V Semiconductors Grown on InP/Si and Ge/Si Wafer Bonded Epitaxial Templates with Application to a Four-Junction Solar Cell, (Abstract), MRS 2003 Spring Meeting, (04/2003)	
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SA	A64	MORRAL et al., The Role of Hydrogen in H-Induced Exfoliation and Layer Transfer on InP, (Abstract), MRS 2004 Spring Meeting, (04/2004)	

Examiner Signature	/Shamim Ahmed/ (08/20/2006)	Date Considered	08/20/2006
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	B2	5,217,564		BOZLER et al.	06-08-1993	
	B3	5,391,257		SULLIVAN et al.	02-21-1995	
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	B21	6,908,828		LETERTRE et al.	06-21-2005	

U.S. PATENT APPLICATIONS					
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Application Document	Name of Patentee or Applicant of Cited Document	Filing Date if Appropriate MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number			
SA	B22	10/761,918	ATWATER et al.	01/20/2004	
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	B25	JP	03-270220		FUJITSU LTD.	02/12/1991		Abst.

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SA	B26	WELDON et al., "Mechanism of Silicon Exfoliation Induced by Hydrogen/Helium Co-Implantation," Applied Physics Letters, Vol. 73, No. 25, December 21, 1998, pgs. 3721-3723.			

Examiner Signature /Shamim Ahmed/ (08/20/2006) Date Considered 08/20/2006

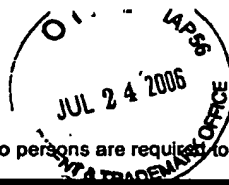
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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

Date Submitted: 7/24/06

(use as many sheets as necessary)

**Complete if Known**

Application Number	10/784,586
Filing Date	2/23/2004
First Named Inventor	Harry A. Jr. ATWATER
Group Art Unit	1765
Examiner Name	S. Ahmed
Attorney Docket Number	047071-0109

Sheet 1 of 1

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SA	C1	2005/0085049	A1	ATWATER, JR. et al.	04/21/2005	
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**UNPUBLISHED U.S. PATENT APPLICATION DOCUMENTS**

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		Serial Number	Kind Code <sup>2</sup> (if known)			
SA	C11	11/430,160		ATWATER, JR. et al.	5/9/2006	

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